

In the Claims

Please amend claims 3, 7, 9-16 as follows:

A1 3. ☐ (Amended) An etching agent for copper according to Claim 1, wherein [the] a concentration of said potassium hydrogen peroxomonosulfate falls within a range of 0.08 to 2.0 mol/l.

A2 7. ☐ (Amended) An etching agent for a laminated film of a titanium film and a copper film comprising an aqueous solution containing a peroxomonosulfate salt, hydrofluoric acid, and one of hydrochloric acid [or] and a chloride.

A3 9. ☐ (Amended) An etching agent for a laminated film of a titanium film and a copper film according to Claim 7, wherein said peroxosulfate salt comprises [any one or more compounds] a compound selected from KHSO_5 , NaHSO_5 , $\text{K}_2\text{S}_2\text{O}_8$, $\text{Na}_2\text{S}_2\text{O}_8$ and $(\text{NH}_4)_2\text{S}_2\text{O}_8$.

10. ☐ (Amended) An etching agent for a laminated film of a titanium film and a copper film according to Claim 7, wherein said chloride comprises one of an alkali metal chloride [or] and ammonium chloride.

11. ☐ (Amended) An etching agent for a laminated film of a titanium film and a copper film according to Claim 8, wherein said peroxosulfate salt comprises [any one or more compounds] a compound selected from KHSO_5 , NaHSO_5 , $\text{K}_2\text{S}_2\text{O}_8$, $\text{Na}_2\text{S}_2\text{O}_8$ and $(\text{NH}_4)_2\text{S}_2\text{O}_8$.

12. ☐ (Amended) An etching agent for a laminated film of a titanium film and a copper film according to Claim 8, wherein said fluoride comprises one of an alkali metal fluoride [or] and ammonium fluoride.

13. ☐ (Amended) A method for manufacturing an electronic device substrate comprising [the steps of]: depositing a copper film on the substrate; forming a given pattern on [the] a surface of the copper film; and etching the copper film using an etching agent comprising an aqueous solution containing potassium hydrogen peroxomonosulfate to form a copper wiring with a given pattern.

14. ☐ (Amended) A method for manufacturing an electronic device substrate comprising [the steps of] forming a mask with a given pattern on [the] a surface of a laminated film prepared by sequentially depositing one of a titanium [or] and titanium

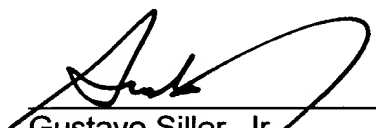
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A3 alloy film, and a copper film on a substrate; and etching the laminated film [comprising the titanium or titanium alloy film and the copper film] using [either] one of an [etching] etching agent comprising an aqueous solution containing potassium hydrogen peroxomonosulfate and hydrofluoric acid, an etching agent comprising an aqueous solution containing a peroxosulfate salt and one of hydrochloric acid [or] and a chloride, [or] and an etching agent comprising an aqueous solution containing a peroxosulfate salt and a fluoride to form a laminated wiring with the given pattern.

15. [Amended] An electronic device comprising an electronic device substrate prepared by a manufacturing method comprising [the steps of]: depositing a copper film on a substrate; forming a mask with a given pattern on the copper film; and etching the copper film using an etching agent comprising an aqueous solution containing potassium hydrogen peroxomonosulfate to form a copper wiring with a given pattern.

16. [Amended] An electronic device comprising an electronic device substrate manufactured by a manufacturing method comprising [the steps of]: forming a mask with a given pattern on a laminated film prepared by sequentially depositing one of a titanium [or] and titanium alloy film and a copper film on a substrate; and etching the laminated film [of the titanium or titanium alloy film and the copper film] using [either] one of an etching agent comprising an aqueous solution containing potassium hydrogen peroxomonosulfate and hydrofluoric acid, an etching agent comprising an aqueous solution containing a peroxosulfate salt, hydrofluoric acid, and one of hydrochloric acid [or] and a chloride, [or] and an etching agent comprising an aqueous solution containing a peroxosulfate salt and a fluoride to form a laminated wiring with the given pattern.

Respectfully submitted,


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